

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

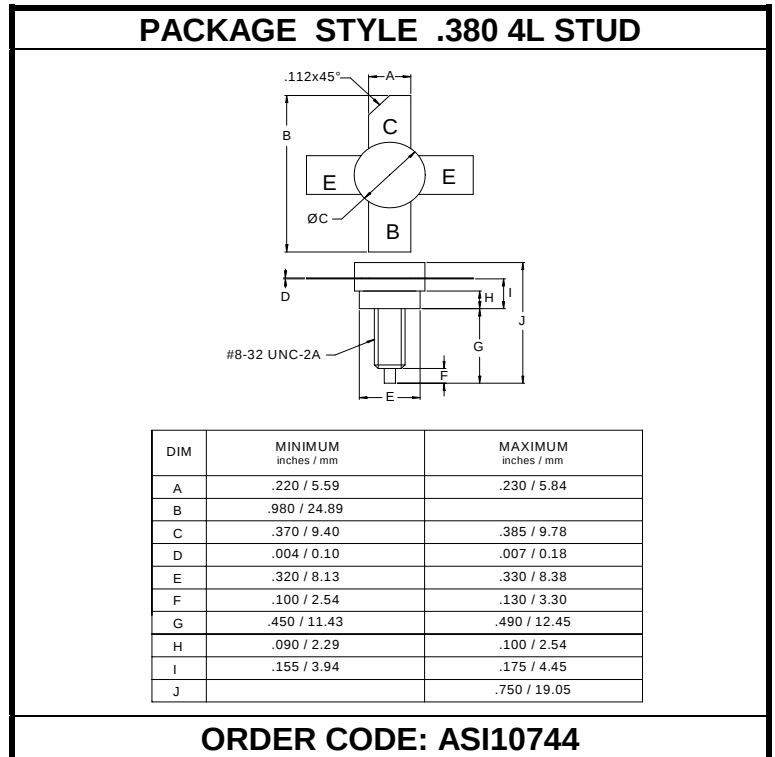
The **ASI VMB40-12S** is Designed for 12.5 V, Medium Band Class C Application.

FEATURES:

- Common Emitter
- $P_G = 10$ dB at 40 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CBO}	36 V
V_{CEO}	18 V
V_{EBO}	4.0 V
P_{DISS}	70 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	2.5 $^\circ\text{C/W}$



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	18			V
BV_{CES}	$I_C = 50$ mA	36			V
BV_{CBO}	$I_C = 50$ mA	36			
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_{CE} = 12.5$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 5.0$ A	20		200	---
C_{OB}	$V_{CB} = 12.5$ V $f = 1.0$ MHz			165	pF
P_G η_C	$V_{CE} = 12.5$ V $P_{OUT} = 40$ W $f = 175$ MHz	10	60		dB %